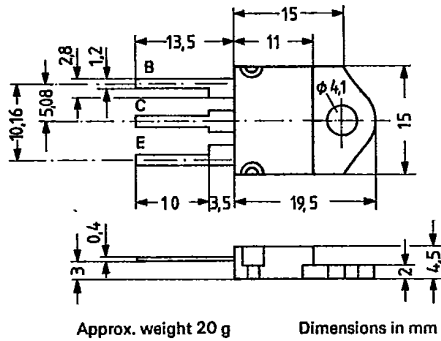


BU 426 and BU 426 A are triple diffused silicon power switching transistors in SOT 93 case (TOP 3). They are outstanding for short switching times and high dielectric strength and are particularly suitable for use in power supply units of TV receivers. The collector is electrically connected to the metallic mounting flange.

Type	Ordering code
BU 426	Q68000-A5164
BU 426 A	Q68000-A5165



Maximum ratings		BU 426	BU 426 A	
Collector-emitter peak voltage	V_{CESM}	800	900	V
Collector-emitter voltage	V_{CEO}	375	400	V
Emitter-base voltage	V_{EBO}	7	7	V
Collector current	I_C	6	6	A
Collector peak current ($t_p \leq 2$ ms)	I_{CM}	8	8	A
Base current	I_B	2	2	A
Base peak current	I_{BM}	3	3	A
Negative base current ($t < 20$ ms)	$-I_B$	0.1	0.1	A
Negative base peak current at turning off	$-I_{BM}$	3	3	A
Emitter current	I_E	6	6	A
Emitter-peak current	I_{EM}	8	8	A
Junction temperature	T_j	150	150	°C
Storage temperature range	T_{stg}	-65 to +150		°C
Total power dissipation ($T_{case} \leq 73$ °C)	P_{tot}	70	70	W

Thermal resistance		BU 426	BU 426 A	
Junction to case	R_{thJC}	≤ 1.1	≤ 1.1	K/W

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Static characteristics ($T_j = 25^\circ\text{C}$)

		BU 426	BU 426 A	
Collector cutoff current ($V_{BE} = 0, V_{CE} = 800\text{ V}$)	I_{CES}	≤ 1	≤ 1	mA
($V_{BE} = 0, V_{CE} = 800\text{ V}, T_j = 125^\circ\text{C}$)	I_{CES}	≤ 2	≤ 2	mA
Emitter cutoff current ($I_C = 0, V_{EB} = 7\text{ V}$)	I_{EBO}	≤ 10	≤ 10	mA
Collector-emitter breakdown voltage ($I_B = 0, I_C = 100\text{ mA}, L = 25\text{ mH}$)	$V_{(BR)CEO}$	≥ 375	≥ 400	V
Collector-emitter saturation voltage ($I_C = 2.5\text{ A}, I_B = 0.5\text{ A}$)	V_{CEsat}	≤ 1.5	≤ 1.5	V
($I_C = 4.0\text{ A}, I_B = 1.25\text{ A}$)	V_{CEsat}	≤ 3	≤ 3	V
Base-emitter saturation voltage ($I_C = 2.5\text{ A}, I_B = 0.5\text{ A}$)	V_{BEsat}	≤ 1.4	≤ 1.4	V
($I_C = 4.0\text{ A}, I_B = 1.25\text{ A}$)	V_{BEsat}	≤ 1.6	≤ 1.6	V
DC current gain ($V_{CE} = 5\text{ V}, I_C = 0.6\text{ A}$)	h_{FE}	30	30	-

Dynamic characteristics

Transition frequency ($V_{CE} = 10\text{ V}, I_C = 0.2\text{ A}, f = 1\text{ MHz}$)	f_T	6	6	MHz
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